# MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

# High Voltage Power Transistors

## **DPAK for Surface Mount Applications**

Designed for line operated audio output amplifier, switchmode supply drivers and other switching applications.

#### Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS

			-	
Rating	Symbol	Max	Unit	
Collector–Emitter Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V <sub>CEO</sub>	250 400	Vdc	
Collector-Base Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V <sub>CB</sub>	350 500	Vdc	
Emitter-Base Voltage	$V_{EB}$	5	Vdc	
Collector Current – Continuous	Ι <sub>C</sub>	1	Adc	
Collector Current – Peak	I <sub>CM</sub>	2	Adc	
Base Current	Ι <sub>Β</sub>	0.6	Adc	
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	15 0.12	W W/°C	
Total Power Dissipation (Note 1) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.56 0.0125	W W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C	
ESD – Human Body Model	HBM	3B	V	
ESD – Machine Model	MM	С	V	
Strangen even ding these listed in the Maximum Datings table may demage the				

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

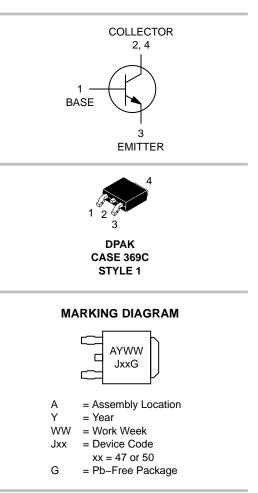
 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



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### NPN SILICON POWER TRANSISTORS 1 AMPERE 250, 400 VOLTS, 15 WATTS



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

### MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Case	$R_{ extsf{ heta}JC}$	8.33	°C/W
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	80	°C/W
Lead Temperature for Soldering Purpose	ΤL	260	°C

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

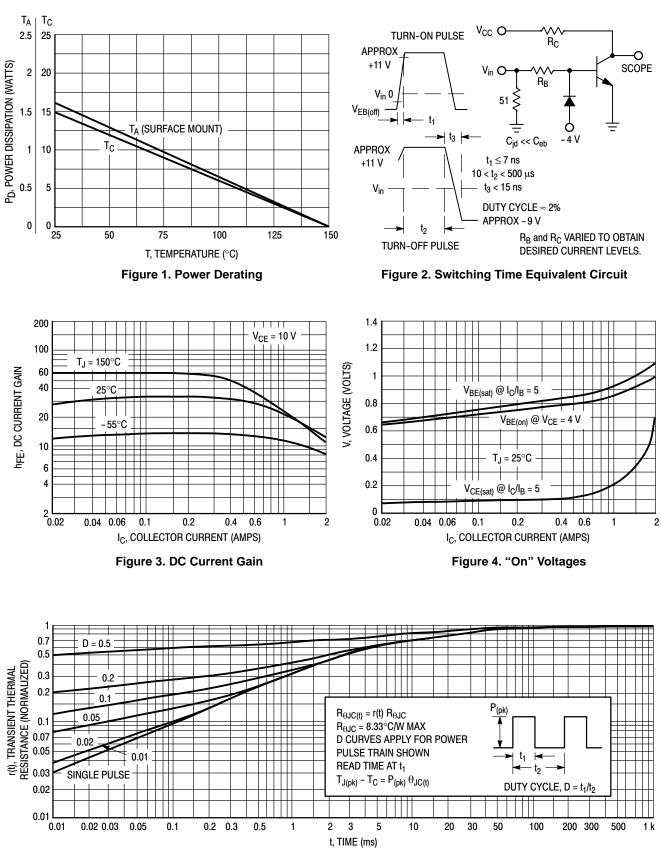
#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = $25^{\circ}$ C unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0) MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V <sub>CEO(sus)</sub>	250 400		Vdc
Collector Cutoff Current ( $V_{CE} = 150 \text{ Vdc}, I_B = 0$ ) MJD47, NJVMJD47T4G ( $V_{CE} = 300 \text{ Vdc}, I_B = 0$ ) MJD50, NJVMJD50T4G	I <sub>CEO</sub>	-	0.2	mAdc
Collector Cutoff Current ( $V_{CE} = 350 \text{ Vdc}, V_{BE} = 0$ ) MJD47, NJVMJD47T4G ( $V_{CE} = 500 \text{ Vdc}, V_{BE} = 0$ ) MJD50, NJVMJD50T4G	ICES	-	0.1	mAdc
Emitter Cutoff Current ( $V_{BE} = 5 \text{ Vdc}, I_C = 0$ )	I <sub>EBO</sub>	_	1	mAdc
ON CHARACTERISTICS (Note 3)				-
DC Current Gain ( $I_C = 0.3 \text{ Adc}, V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}$ )	h <sub>FE</sub>	30 10	150 -	_
Collector–Emitter Saturation Voltage $(I_{C} = 1 \text{ Adc}, I_{B} = 0.2 \text{ Adc})$	V <sub>CE(sat)</sub>	_	1	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc)	V <sub>BE(on)</sub>	-	1.5	Vdc
DYNAMIC CHARACTERISTICS			•	•
Current Gain – Bandwidth Product (I <sub>C</sub> = 0.2 Adc, V <sub>CE</sub> = 10 Vdc, f = 2 MHz)	f <sub>T</sub>	10	-	MHz
Small–Signal Current Gain (I <sub>C</sub> = 0.2 Adc, V <sub>CE</sub> = 10 Vdc, f = 1 kHz)	h <sub>fe</sub>	25	_	-

3. Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2%.

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**TYPICAL CHARACTERISTICS** 



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Figure 5. Thermal Response

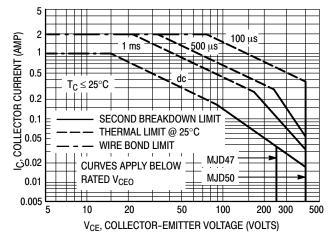
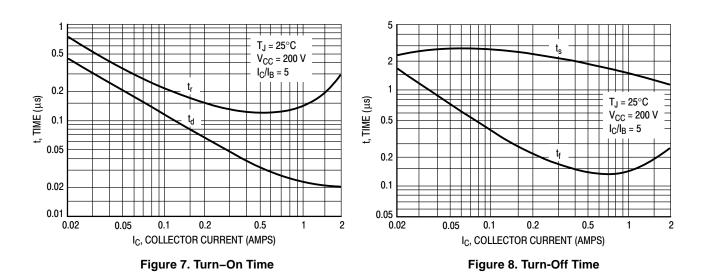


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



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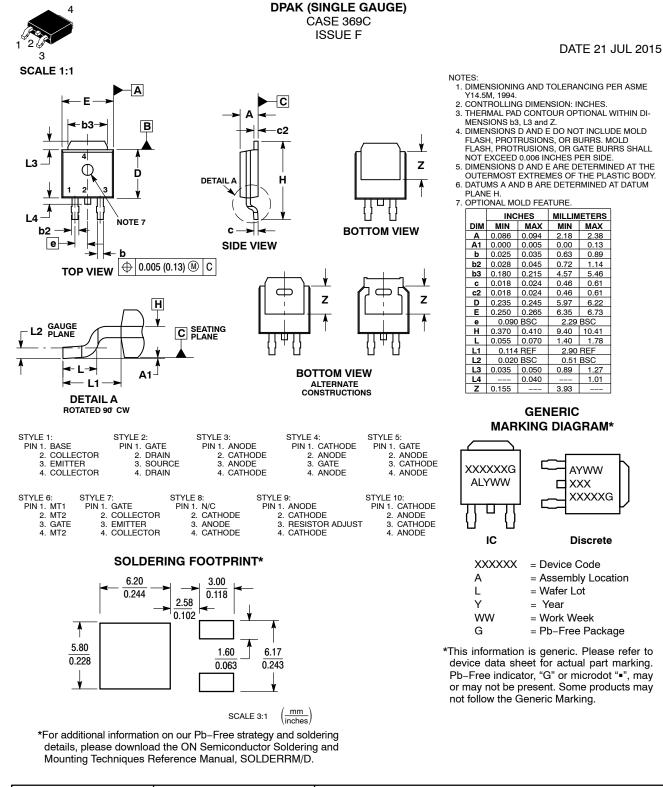
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MJD47G	369C (Pb-Free)	75 Units / Rail
MJD47T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD47T4G*	369C (Pb-Free)	2,500 / Tape & Reel
MJD50G	369C (Pb-Free)	75 Units / Rail
MJD50T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD50T4G*	369C (Pb-Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D. \*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

Capable.

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